

10th International Symposium on Display Holography (ISDH'2015) 28 June - 3 July, 2015, St. Petersburg

# DIRECT LASER RECORDING OF DOT HOLOGRAMS ON AMORPHOUS SILICON FILM

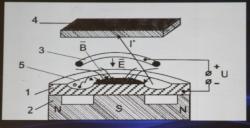
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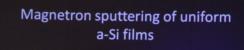
#### Outline

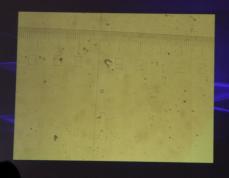
- 1. Introduction
- Magnetron sputtering of amorphous silicon film and study of their absorption spektra
- 3. Scanning laser writing system
- 4. Direct laser recording to a-Si by Blue ray laser
- 5. Relief measurement
- 6. Summary

## Vacuum planar equipment for magnetron sputtering of metallic films



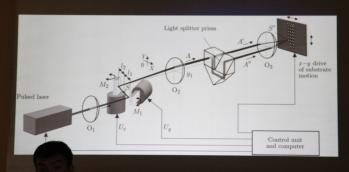
- 1 катод-мишень;
- 2 магнитная система;
- 3 анод;
- 4 подложка;
- 5 зона распыления



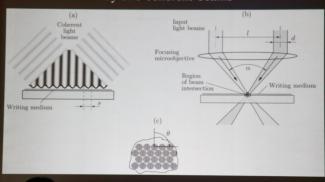


#### Optical scheme of the SIL writing channel

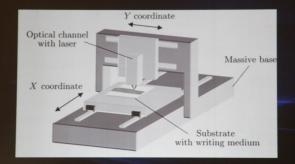
Eurasian Patent No. 007874, Publ. 2007, Bul. No. 1. "Device for Writing Diffractive Elements"

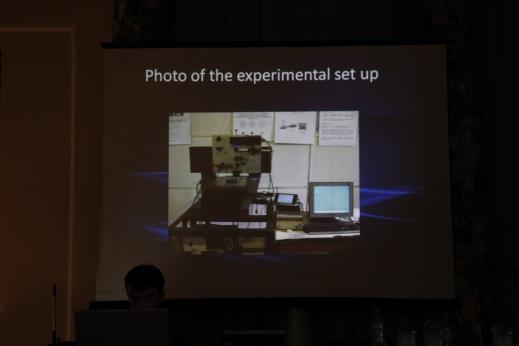


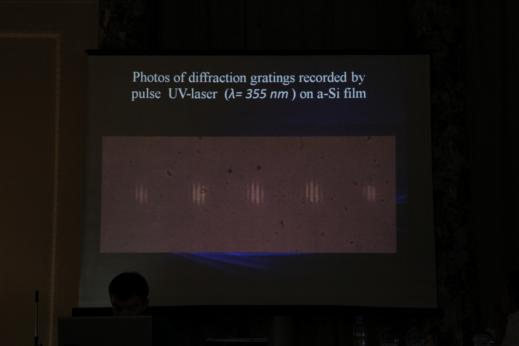
# Formation of the periodic structure by two coherent beams



#### Structure of the system of interference lithography









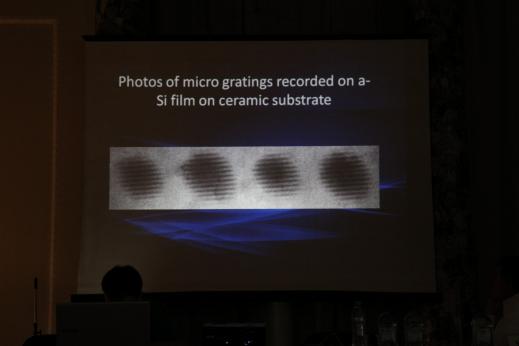


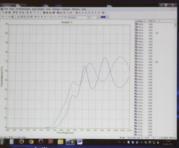
Photo of diffractive elements recorded on a-Si film on glass substrate

# The absorption spectra of a-Si films with different thickness



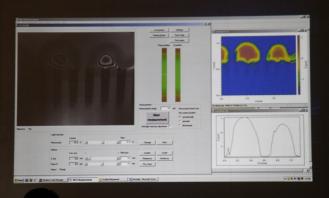


Условия записи: Длина волны – 532нм; Скорость вращения – 12 об/сек Размер пучка – 0.5 мкм (FWHM) R=5мм (Объектив 25х) 40/2/20 Pref=65 Changing the refractive index of the silicon film under the laser radiation interaction. The shift of the transmission spectrum maxima is appear.

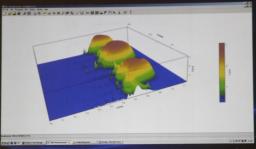


The red curve – unexposed silicon
Blue curve - the exposed portion (5x5 mm square) Spectrophotometer UNICO 2800.

Measurement of recorded sample on scanning interferometric microscope in white light VLI regime – on reflection. Objective – 50x

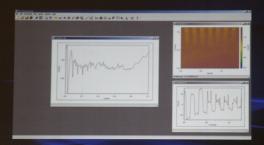


#### 3D image

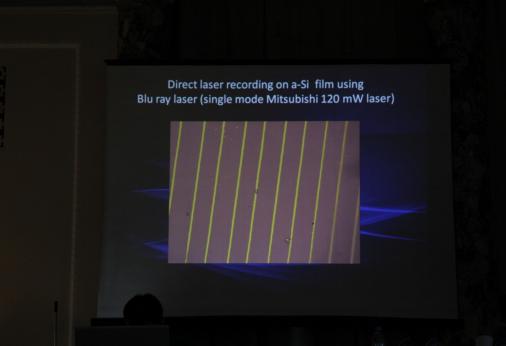


Under interaction of laser radiation amorphous silicon transforming to crystalline silicon with volume increasing. Distance between atoms of a-si :  $1.54A^0$ , for \*alline silicon distance between atoms :  $5.431A^0$ .

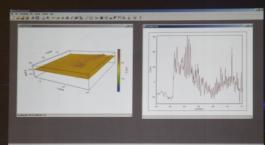
#### Measurement of recorded relief



under laser radiation interaction relief formed with value 20 -30 HM.

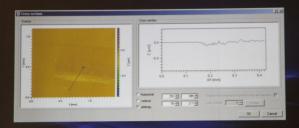


#### **Relief Measurement**



VLI Lab Wight light interferometer 10x – objective

### Relief Measurement



#### **Possible applications**

- Dot Matrix Holograms Fabrication
- Interference lithography
- Digital Holography
- Security applications (read only security ID cards)
- Antireflective Submicrometer Surface-Relief Gratings

#### Summary

- Developed Direct laser recording on a -Si film provides following advantages: fast process of recording by pulse UV-laser and it's not require chemical processing; high resolution; read only process without rewriting opportunity
- developed scanning system of interference lithography provide diffractive microstructures recording from microgratings with an arbitrary orientation and a period of 0.6 to 1.5 m with a total size up to 300 mm
- It was demonstrated possibilities of direct laser recording by laser radiation with λ= 355nm, λ= 405nm and λ= 532nm
- Possible application:
   Dot Matrix Holograms Fabrications
  - Interference lithography
  - Security applications (read only security ID cards)
  - Antireflective Submicrometer Surface-Relief Gratings

